

SANYO	No.2471A	2SC4106
		NPN Triple Diffused Planar Type Silicon Transistor

SWITCHING REGULATOR APPLICATIONS

Features

- . High breakdown voltage and high reliability
- . Fast switching speed
- . Wide ASO
- . Adoption of MBIT process

Absolute Maximum Ratings at Ta=25°C

			unit
Collector-to-Base Voltage	V _{CB0}	500	V
Collector-to-Emitter Voltage	V _{CE0}	400	V
Emitter-to-Base Voltage	V _{EB0}	7	V
Collector Current	I _C	7	A
Peak Collector Current	i _{cp}	PW ≤ 300μs, duty cycle ≤ 10%	14 A
Base Current	I _B	3	A
Collector Dissipation	P _C	1.75	W
		Tc=25°C	50 W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CBO}	V _{CB} =400V, I _E =0			10	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} =5V, I _C =0			10	μA
DC Current Gain	h _{FE} (1)	V _{CE} =5V, I _C =0.8A	15*		50*	
	h _{FE} (2)	V _{CE} =5V, I _C =4A	10			
	h _{FE} (3)	V _{CE} =5V, I _C =10mA	10			
C-E Saturation Voltage	V _{CE(sat)}	I _C =4A, I _B =0.8A			0.8	V
B-E Saturation Voltage	V _{BE(sat)}	I _C =4A, I _B =0.8A			1.5	V
Gain-Bandwidth Product	f _T	V _{CE} =10V, I _C =0.8A		20		MHz
Output Capacitance	c _{ob}	V _{CB} =10V, f=1MHz		80		pF

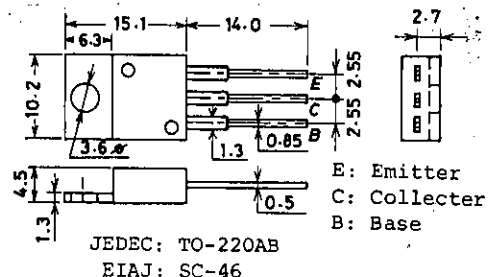
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*: The h_{FE1} of the 2SC4106 is classified as follows. When specifying the h_{FE1} rank, specify two ranks or more in principle.

15 L 30	20 M 40	30 N 50
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Package Dimensions 2010A

(unit:mm)

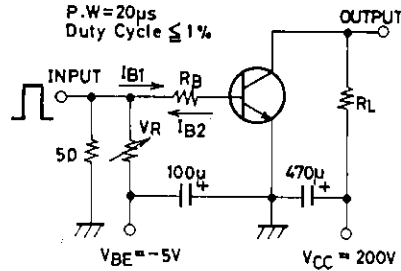


E: Emitter
C: Collector
B: Base

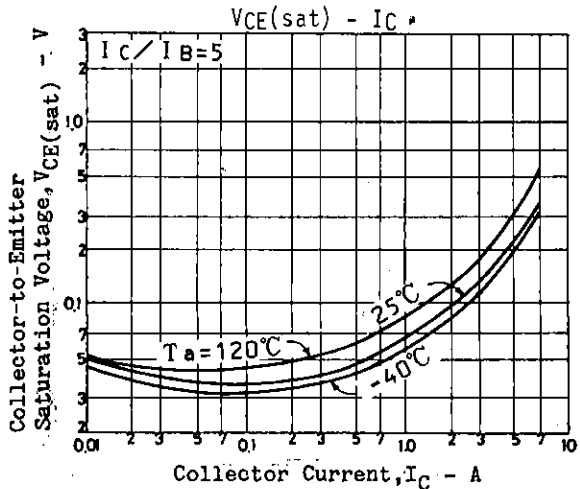
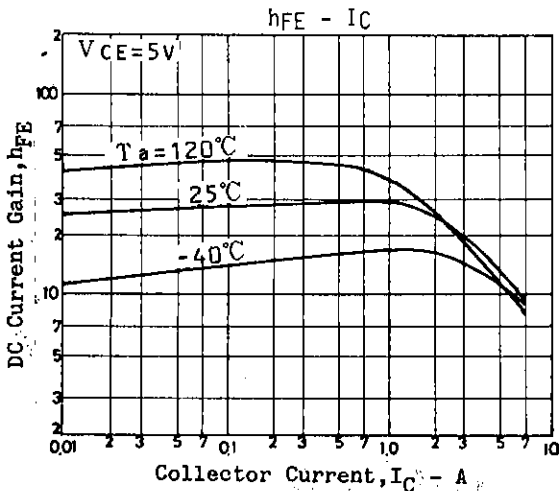
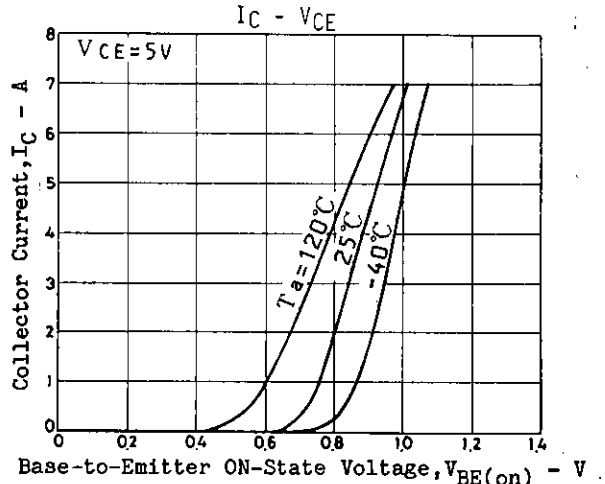
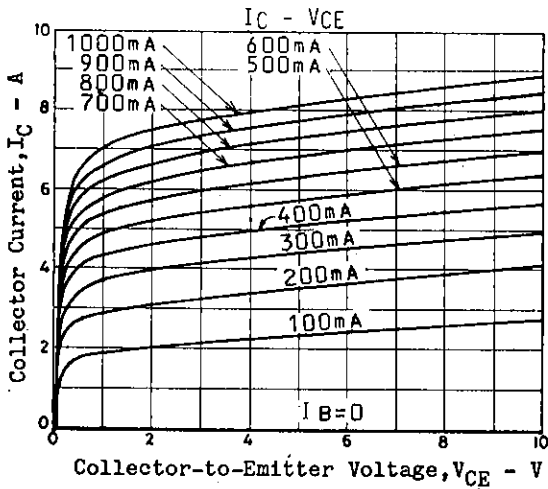
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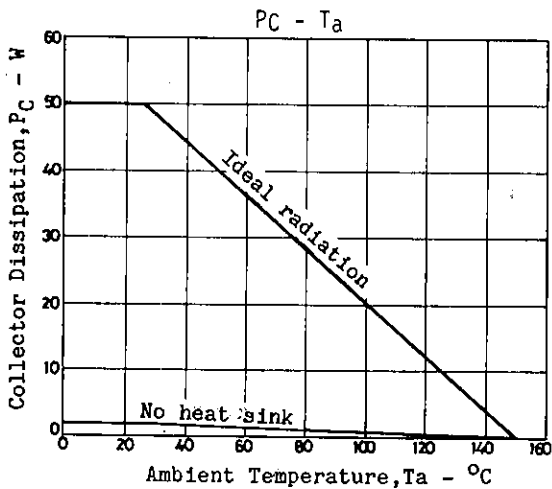
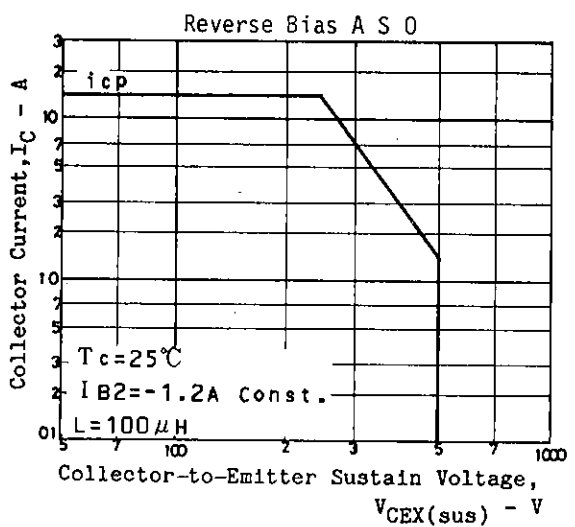
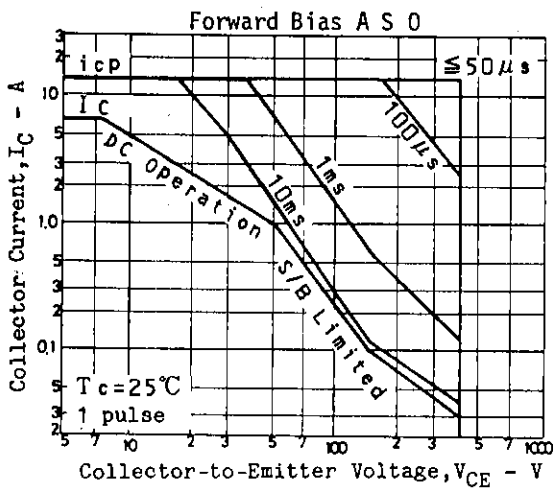
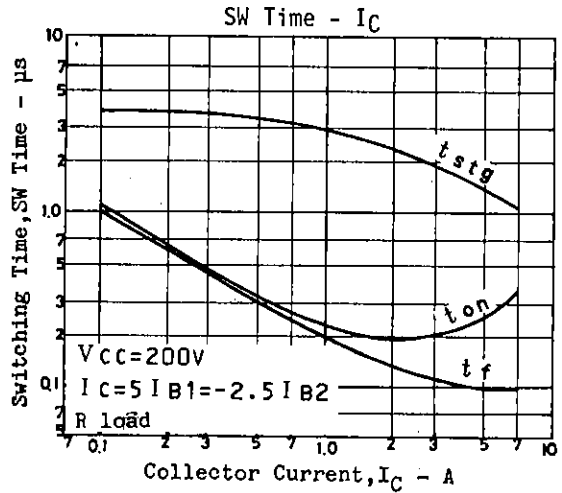
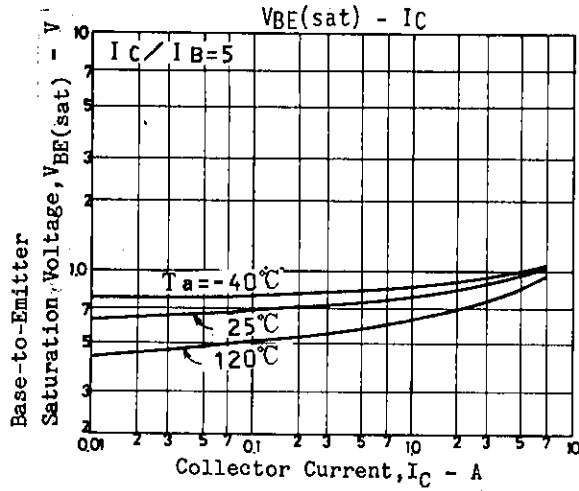
			min	typ	max	unit
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	500			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=5mA, R_{BE}=\infty$	400			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	7			V
C-E Sustain Voltage	$V_{CEX(sus)}$	$I_C=3A, I_{B1}=-0.3A,$ $I_{B2}=-1.2A, L=1mH, \text{clamped}$	400			V
Turn-on Time	t_{on}	$I_C=5A, I_{B1}=1A,$ $I_{B2}=-2A, R_L=40ohms,$ $V_{CC}=200V$		0.5		μs
Storage Time	t_{stg}	$I_C=5A, I_{B1}=1A,$ $I_{B2}=-2A, R_L=40ohms,$ $V_{CC}=200V$		2.5		μs
Fall Time	t_f	$I_C=5A, I_{B1}=1A,$ $I_{B2}=-2A, R_L=40ohms,$ $V_{CC}=200V$		0.3		μs

Switching Time Test Circuit



Unit (Resistance : Ω , Capacitance : F)





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